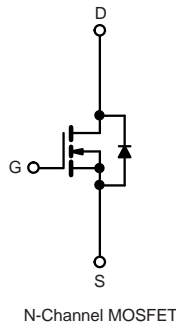
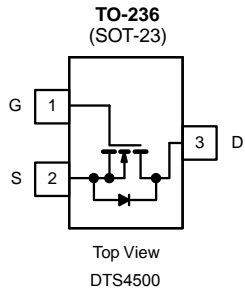


## N-Channel 40 V (D-S) MOSFET

PRODUCT SUMMARY			
$V_{DS}$ (V)	$R_{DS(on)}$ ( $\Omega$ )	$I_D$ (A) <sup>a</sup>	$Q_g$ (Typ.)
40	0.040 at $V_{GS} = 10$ V	3.6	2.9 nC
	0.055 at $V_{GS} = 4.5$ V	3.1	



### FEATURES

- DT-Trench Power MOSFET
- 100 %  $R_g$  Tested
- Compliant to RoHS Directive 2002/95/EC



**RoHS**  
COMPLIANT

### APPLICATIONS

- DC/DC Converters
- Load Switch
- Portable and Consumer Applications

ABSOLUTE MAXIMUM RATINGS ( $T_A = 25$ °C, unless otherwise noted)				
Parameter	Symbol	Limit	Unit	
Drain-Source Voltage	$V_{DS}$	40	V	
Gate-Source Voltage	$V_{GS}$	$\pm 20$		
Continuous Drain Current ( $T_J = 150$ °C)	$I_D$	$T_C = 25$ °C	3.6 <sup>a</sup>	A
		$T_C = 70$ °C	2.5	
		$T_A = 25$ °C	3.3 <sup>b, c</sup>	
		$T_A = 70$ °C	2.5 <sup>b, c</sup>	
Pulsed Drain Current	$I_{DM}$	20		
Continuous Source-Drain Diode Current	$I_S$	$T_C = 25$ °C	1.75	
		$T_A = 25$ °C	1.04 <sup>b, c</sup>	
Maximum Power Dissipation	$P_D$	$T_C = 25$ °C	2.1	W
		$T_C = 70$ °C	1.3	
		$T_A = 25$ °C	1.25 <sup>b, c</sup>	
		$T_A = 70$ °C	0.8 <sup>b, c</sup>	
Operating Junction and Storage Temperature Range	$T_J, T_{stg}$	- 55 to 150	°C	
Soldering Recommendations (Peak Temperature)		260		

THERMAL RESISTANCE RATINGS					
Parameter	Symbol	Typical	Maximum	Unit	
Maximum Junction-to-Ambient <sup>b, d</sup>	$R_{thJA}$	80	100	°C/W	
Maximum Junction-to-Foot (Drain)	$R_{thJF}$	40	60		

Notes:

- Based on  $T_C = 25$  °C
- Surface mounted on 1" x 1" FR4 board.
- $t = 5$  s.
- Maximum under steady state conditions is 125 °C/W.

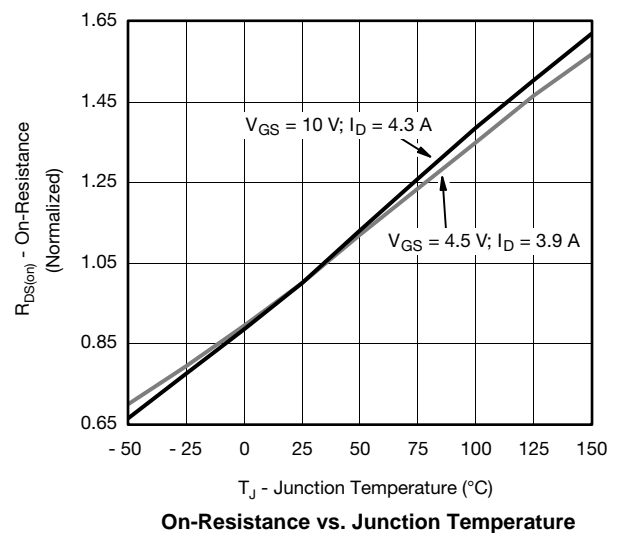
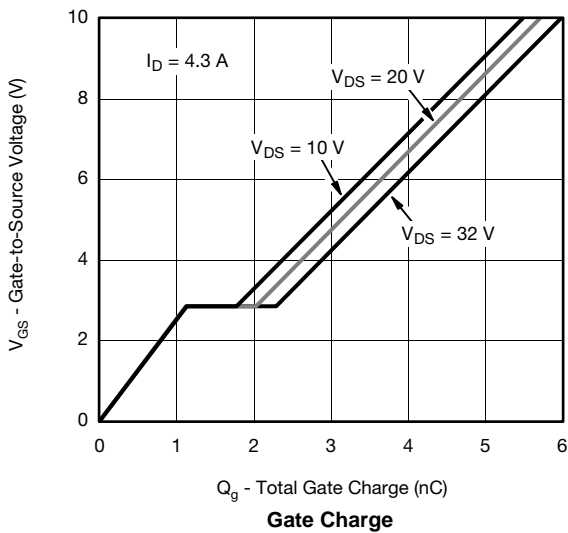
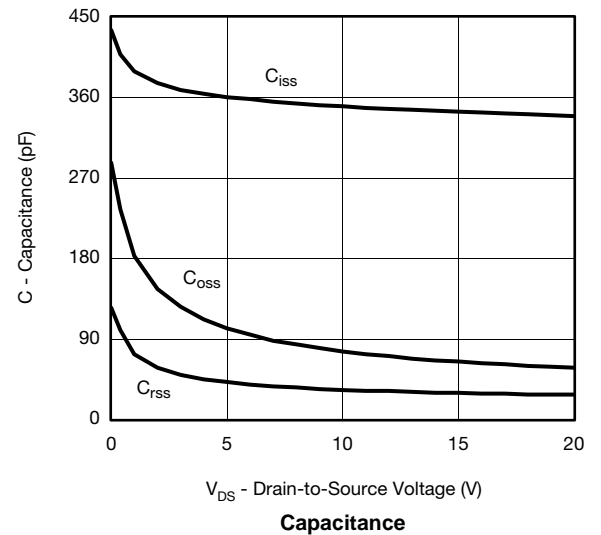
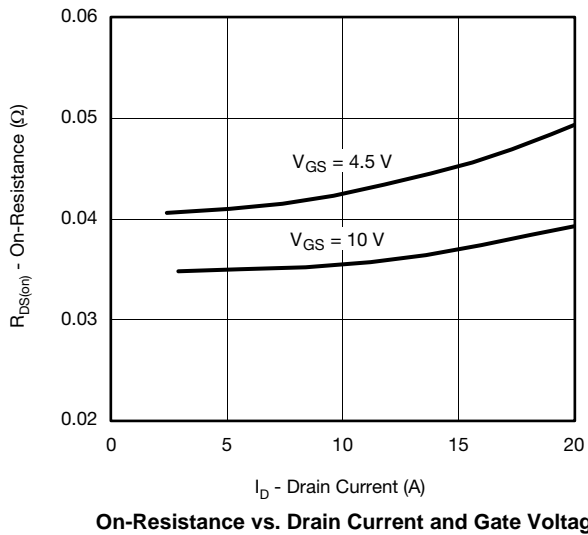
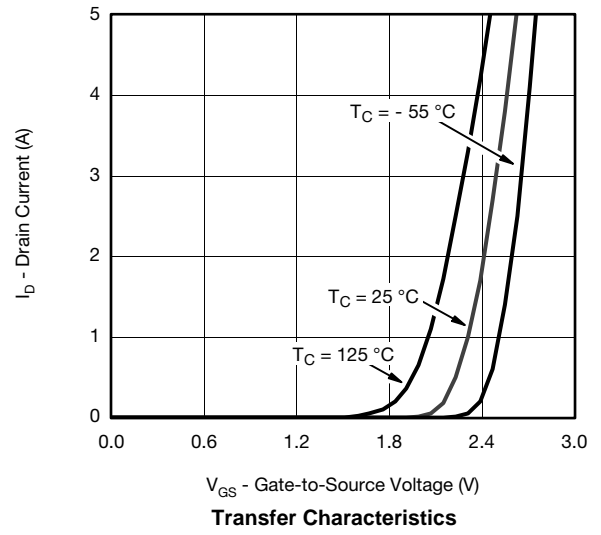
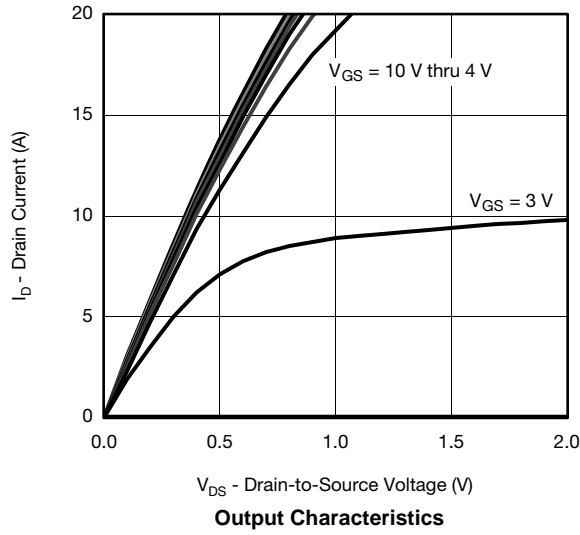
<b>SPECIFICATIONS</b> ( $T_J = 25\text{ }^\circ\text{C}$ , unless otherwise noted)						
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
<b>Static</b>						
Drain-Source Breakdown Voltage	$V_{DS}$	$V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$	40			V
$V_{DS}$ Temperature Coefficient	$\Delta V_{DS}/T_J$	$I_D = 250\text{ }\mu\text{A}$		39		mV/°C
$V_{GS(th)}$ Temperature Coefficient	$\Delta V_{GS(th)}/T_J$			- 4.7		
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$	0.5		1.5	V
Gate-Source Leakage	$I_{GSS}$	$V_{DS} = 0\text{ V}, V_{GS} = \pm 20\text{ V}$			$\pm 100$	nA
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = 40\text{ V}, V_{GS} = 0\text{ V}$			1	$\mu\text{A}$
		$V_{DS} = 40\text{ V}, V_{GS} = 0\text{ V}, T_J = 70\text{ }^\circ\text{C}$			10	
On-State Drain Current <sup>a</sup>	$I_{D(on)}$	$V_{DS} \leq 5\text{ V}, V_{GS} = 10\text{ V}$	20			A
Drain-Source On-State Resistance <sup>a</sup>	$R_{DS(on)}$	$V_{GS} = 10\text{ V}, I_D = 3.3\text{ A}$		0.035	0.040	$\Omega$
		$V_{GS} = 4.5\text{ V}, I_D = 2.9\text{ A}$		0.041	0.055	
Forward Transconductance <sup>a</sup>	$g_{fs}$	$V_{DS} = 20\text{ V}, I_D = 2.3\text{ A}$		17		S
<b>Dynamic<sup>b</sup></b>						
Input Capacitance	$C_{iss}$	$V_{DS} = 20\text{ V}, V_{GS} = 0\text{ V}, f = 1\text{ MHz}$		340		$\mu\text{F}$
Output Capacitance	$C_{oss}$			60		
Reverse Transfer Capacitance	$C_{rss}$			30		
Total Gate Charge	$Q_g$	$V_{DS} = 20\text{ V}, V_{GS} = 10\text{ V}, I_D = 4.3\text{ A}$		5.8	9	nC
		$V_{DS} = 20\text{ V}, V_{GS} = 4.5\text{ V}, I_D = 4.3\text{ A}$		2.9	6	
Gate-Source Charge	$Q_{gs}$			1.1		
Gate-Drain Charge	$Q_{gd}$			0.9		
Gate Resistance	$R_g$	$f = 1\text{ MHz}$	0.6	3.3	6.6	$\Omega$
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 20\text{ V}, R_L = 5.7\text{ }\Omega$ $I_D \cong 3.5\text{ A}, V_{GEN} = 4.5\text{ V}, R_g = 1\text{ }\Omega$		12	20	ns
Rise Time	$t_r$			50	75	
Turn-Off Delay Time	$t_{d(off)}$			10	20	
Fall Time	$t_f$			8	16	
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 20\text{ V}, R_L = 5.7\text{ }\Omega$ $I_D \cong 3.5\text{ A}, V_{GEN} = 10\text{ V}, R_g = 1\text{ }\Omega$		7	14	
Rise Time	$t_r$			20	30	
Turn-Off Delay Time	$t_{d(off)}$			14	21	
Fall Time	$t_f$			8	16	
<b>Drain-Source Body Diode Characteristics</b>						
Continuous Source-Drain Diode Current	$I_S$	$T_C = 25\text{ }^\circ\text{C}$			1.75	A
Pulse Diode Forward Current	$I_{SM}$				20	
Body Diode Voltage	$V_{SD}$	$I_S = 3.5\text{ A}, V_{GS} = 0\text{ V}$		0.85	1.2	V
Body Diode Reverse Recovery Time	$t_{rr}$	$I_F = 3.5\text{ A}, di/dt = 100\text{ A}/\mu\text{s}, T_J = 25\text{ }^\circ\text{C}$		15	23	ns
Body Diode Reverse Recovery Charge	$Q_{rr}$			7	14	nC
Reverse Recovery Fall Time	$t_a$			11		ns
Reverse Recovery Rise Time	$t_b$			4		

Notes:

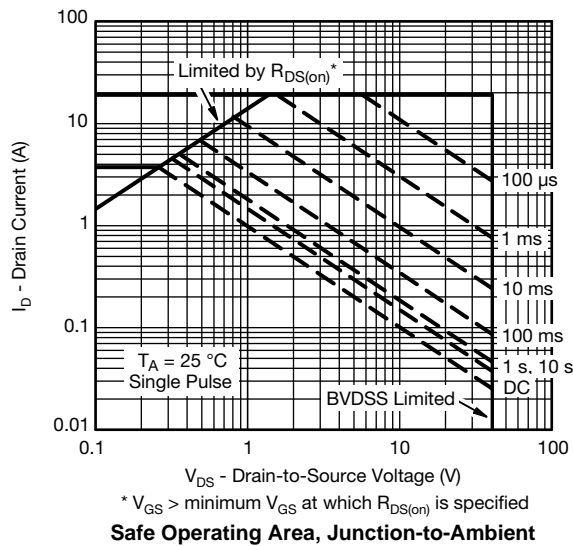
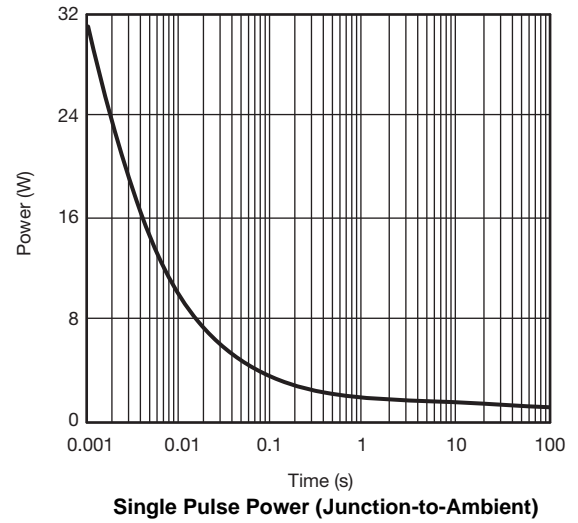
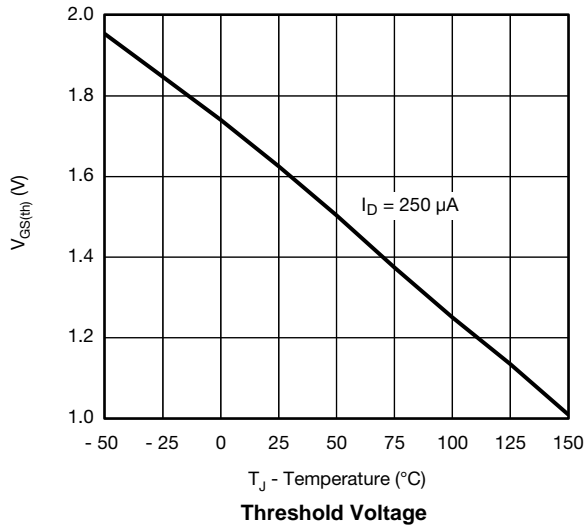
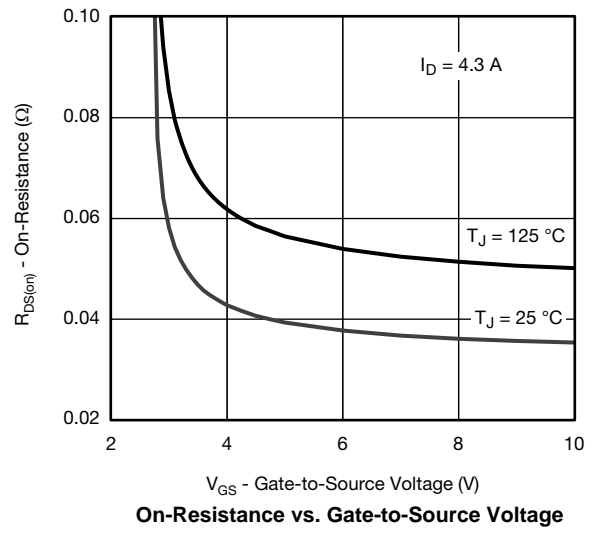
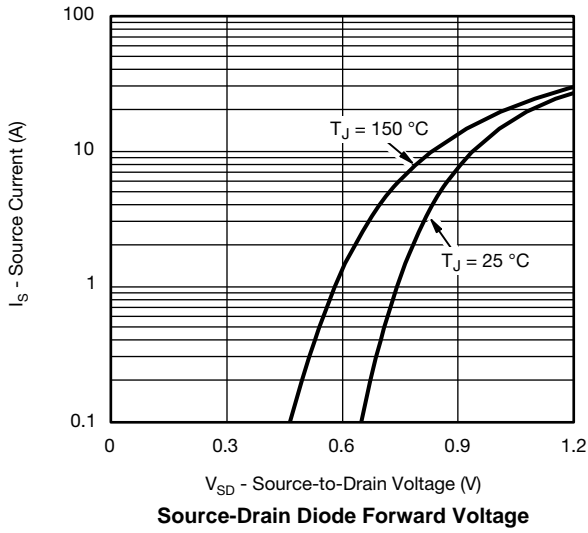
- a. Pulse test; pulse width  $\leq 300\text{ }\mu\text{s}$ , duty cycle  $\leq 2\%$   
 b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

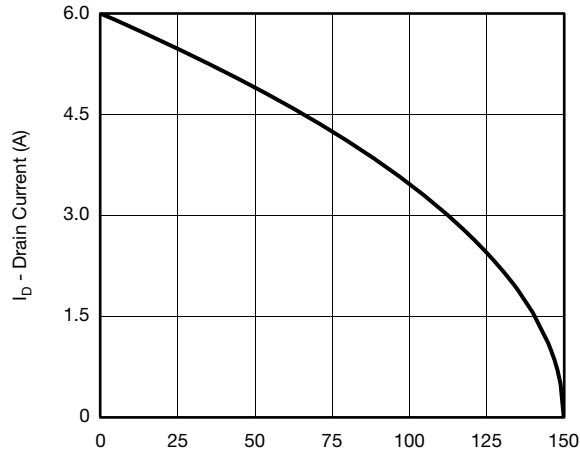
**TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)



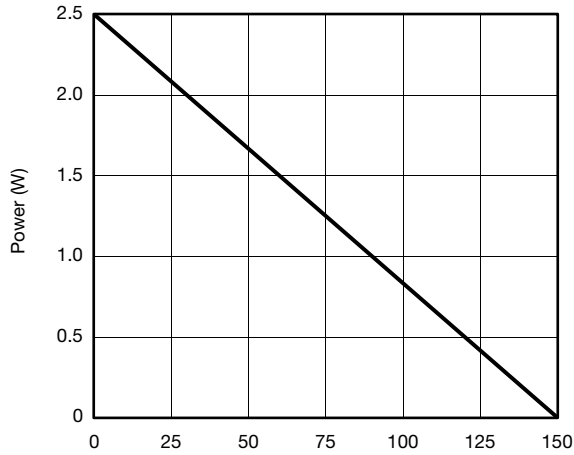
**TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)



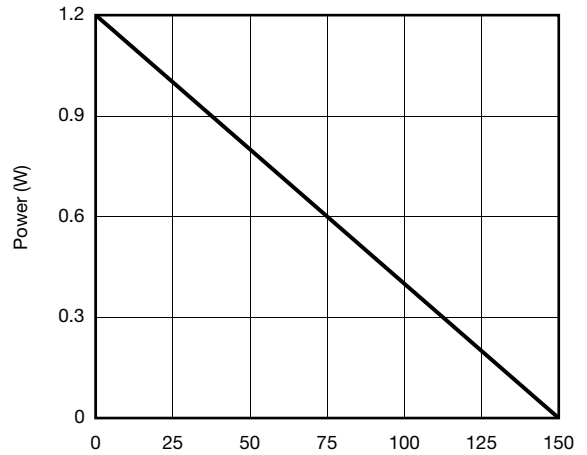
**TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)



$T_C$  - Case Temperature (°C)  
**Current Derating\***



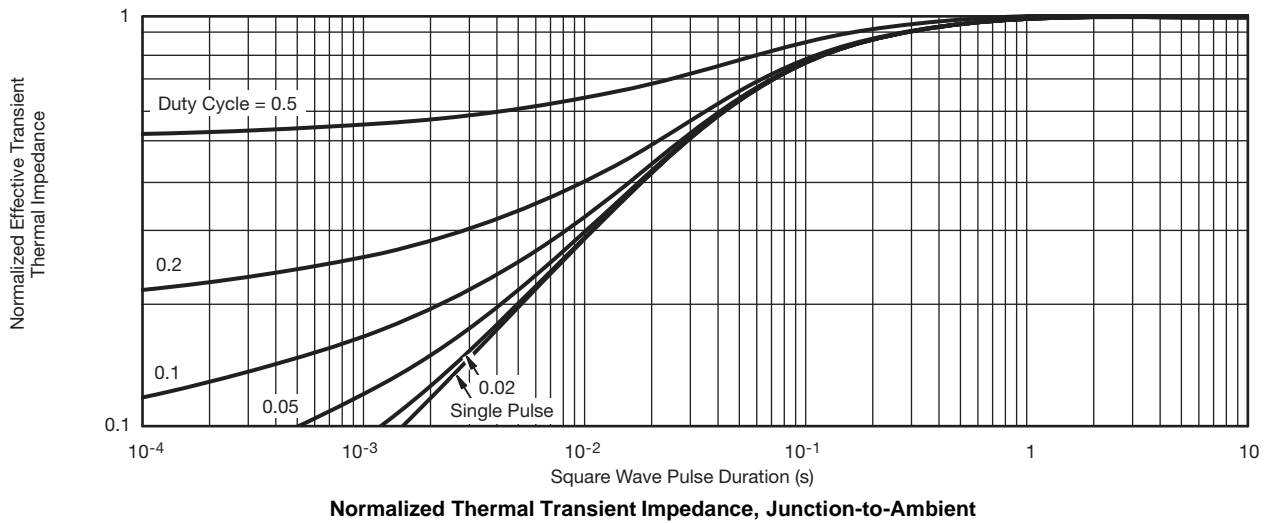
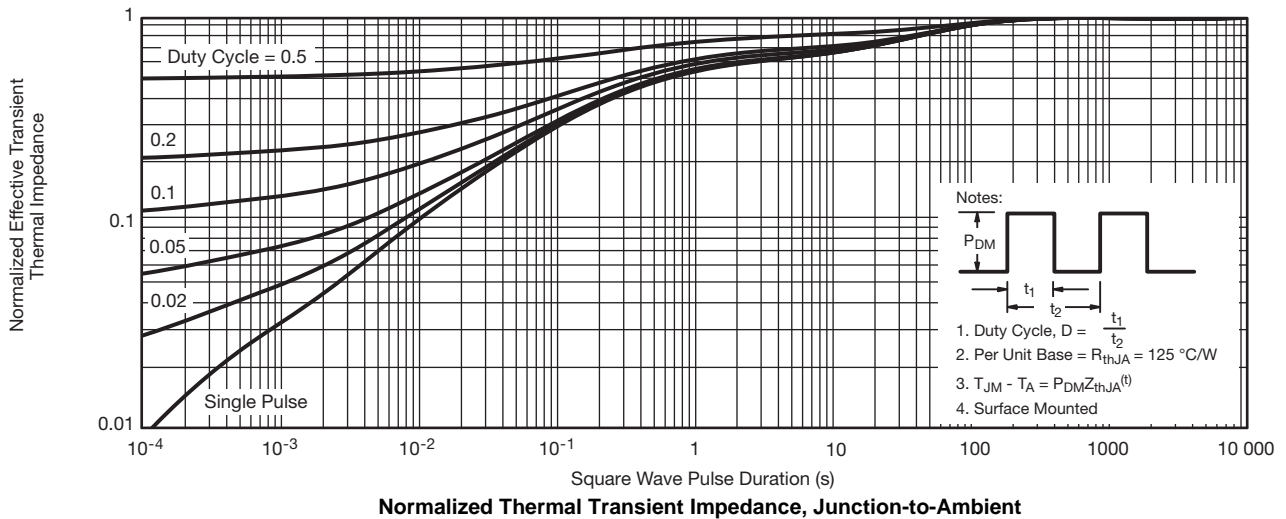
$T_C$  - Case Temperature (°C)  
**Power Derating, Junction-to-Foot**



$T_A$  - Ambient Temperature (°C)  
**Power Derating, Junction-to-Ambient**

\* The power dissipation  $P_D$  is based on  $T_{J(max.)} = 150$  °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

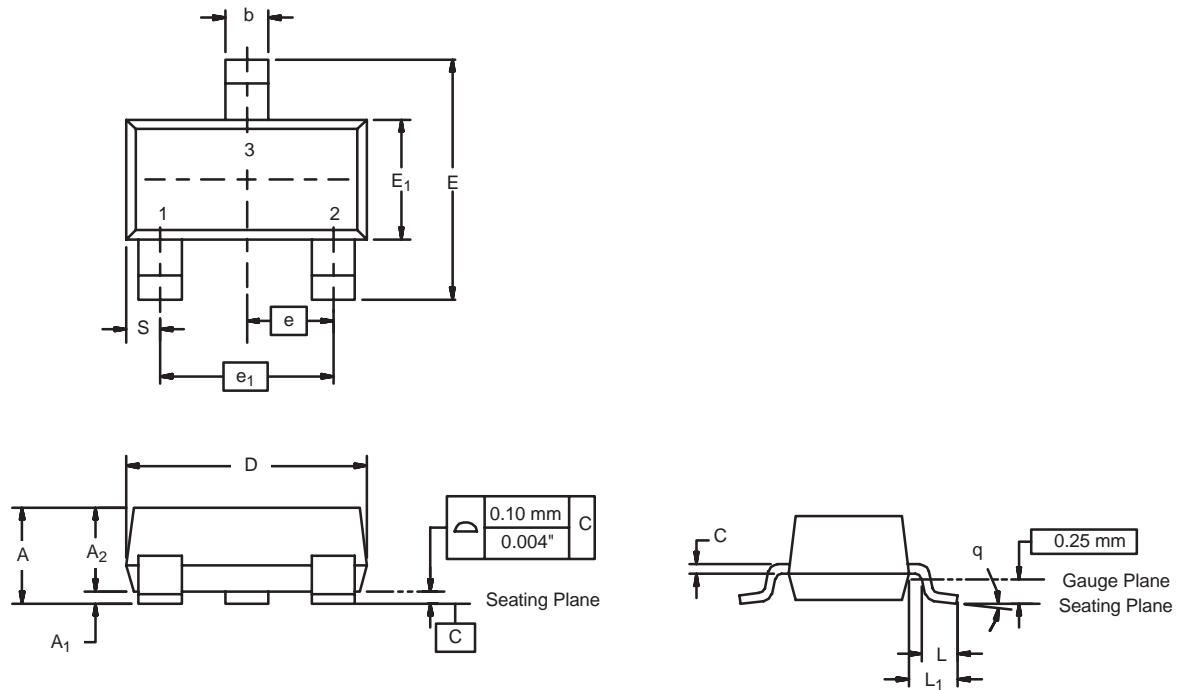
**THERMAL RATINGS** ( $T_A = 25\text{ }^\circ\text{C}$ , unless otherwise noted)



**Note**

- The characteristics shown in the two graphs
  - Normalized Transient Thermal Impedance Junction-to-Ambient ( $25\text{ }^\circ\text{C}$ )
  - Normalized Transient Thermal Impedance Junction-to-Foot ( $25\text{ }^\circ\text{C}$ )
 are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

**SOT-23 (TO-236): 3-LEAD**



Dim	MILLIMETERS		INCHES	
	Min	Max	Min	Max
A	0.89	1.12	0.035	0.044
A <sub>1</sub>	0.01	0.10	0.0004	0.004
A <sub>2</sub>	0.88	1.02	0.0346	0.040
b	0.35	0.50	0.014	0.020
c	0.085	0.18	0.003	0.007
D	2.80	3.04	0.110	0.120
E	2.10	2.64	0.083	0.104
E <sub>1</sub>	1.20	1.40	0.047	0.055
e	0.95 BSC		0.0374 Ref	
e <sub>1</sub>	1.90 BSC		0.0748 Ref	
L	0.40	0.60	0.016	0.024
L <sub>1</sub>	0.64 Ref		0.025 Ref	
S	0.50 Ref		0.020 Ref	
q	3°	8°	3°	8°

ECN: S-03946-Rev. K, 09-Jul-01  
DWG: 5479

**RECOMMENDED MINIMUM PADS FOR SOT-23**



Recommended Minimum Pads  
Dimensions in Inches/(mm)

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